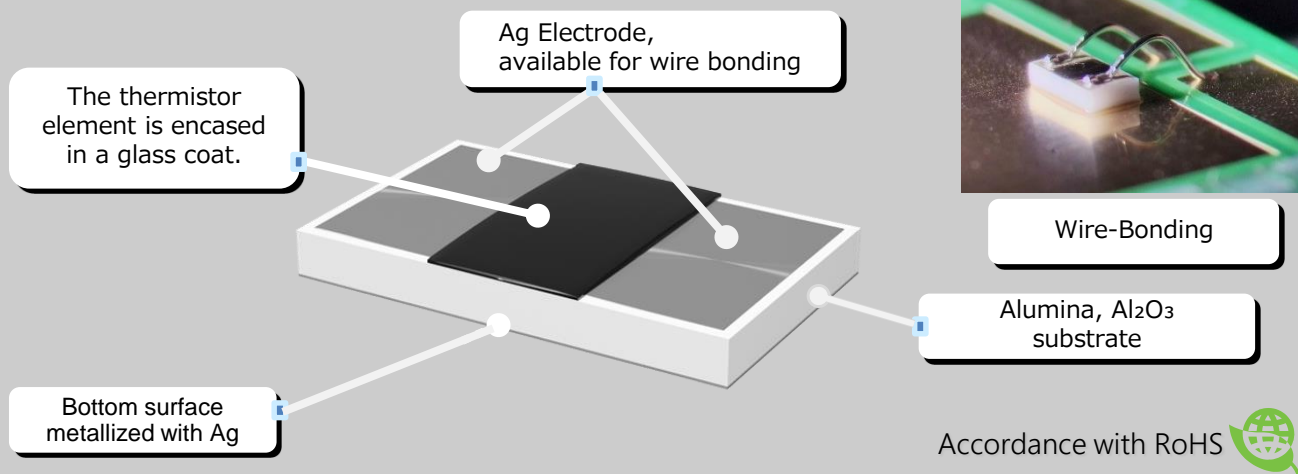




200°C Wire-Bondable Chip Thermistor for SiC/GaN Modules

Engineered for High-Temperature Power Module Applications

Crafted through ingenious material design, precision mixing processes, and safeguarded by patent protection.



Accordance with RoHS



Features

- Optimized for high temperature sensing, control, and compensation.
- Wide temperature ranges from -50°C to +200°C are ideal for SiC and GaN.
- The top surface has two electrodes Ag perfectly suitable for wire bonding.
- The bottom surface is metallized with Ag for sintering.
- Empowered by an Alumina base and Glass coating, ensuring high mechanical strength.
- Unparalleled thermal responsiveness due to its compact cubic volume and exceptional heat capacity.
- Thermal Response: Featuring minimal thermal capacity, yet heightened sensor sensitivity.
- AEC-Q200 compliant product.
- Formic acid reflow compliant product.

Application

- SiC/GaN Power modules
- Inverter for EV and HEV Vehicles
- IGBT (Insulated Gate Bipolar Transistor)
- MOSFET (Metal-Oxide-Semiconductor Field-Effect Transistor)
- DC-DC Converter
- Temperature management of the On-Board Charger
- Temperature compensation of semiconductors
- Automotive ABS control circuit

The product characteristics can be customized according to customer requirements. Please feel free to contact us.

Specification data

Chip size (mm)	Operating temperature	Resistance at 25°C	Resistance tolerance	B Constant (25°C/85°C)	B constant tolerance	Rated power at 25°C	Maximum permissible power	Thermal dissipation constant (in air)
2012mm (0805inch)	-50°C ~ +200°C	1k ~ 500kΩ	±1%, ±2%, ±3%, ±5%, ±10%	3375~4500K	±1%, ±2%, ±3%, ±5%,	130mW	5mW	δ≤1.5mW/°C

※ Please contact us for in case of any other specifications.

